Abstract of the Disclosure

An etching method and an etching apparatus for applying an etchant containing nitric acid and hydrofluoric acid to silicon to etch the silicon. The etchant used in etching is recovered, and brought into contact with a gas inert to the etchant, whereby the etchant is regenerated. At least a part of the regenerated etchant is reused in etching.

This Sheet Has Been Replaced

